



Fig. 8.9. LED with an n-type current-blocking layer located on the upper confinement layer. Light emission occurs in the regions not covered by the opaque top ohmic contact. The LED is fabricated by *epitaxial regrowth*. After growth of the current-blocking layer, the wafer is taken out of the growth system for etching. The wafer is then re-introduced into the epitaxial system for growth of the current-spreading layer.

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### Exhibit A